

1. Material Substrate GaAs (N Type)
 Epitaxial Layer GaAlAs (P/N Type)

2. Electrode N(Cathode) Side Gold Alloy
 P(Anode) Side Gold Alloy

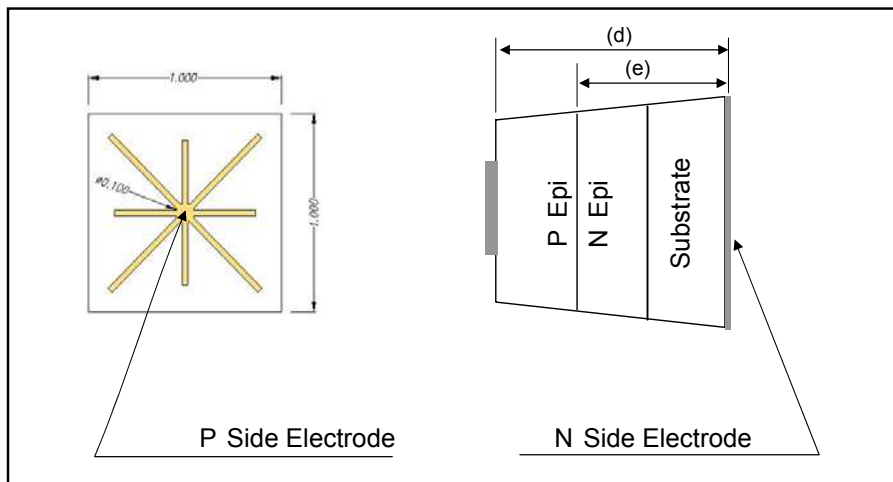
3. Electro-Optical Characteristics

Parameter	Symbo	Min	Typ	Max	Unit	Condition
Forward Voltage	V_F		1.35	1.5	V	IF=350mA
Reverse Voltage	V_R	5			V	IR=10uA
Radiant Power	P_O	12	17		mW	IF=350mA
Wavelength	λ_P		940		nm	IF=20mA
	$\Delta\lambda$		45		nm	IF=20mA

※ Note : LED Chip is mounted on TO-18 gold header without resin coating.

4. Mechanical Data

(a) Emission Area	-----	39.0mil x	39.0mil
(b) Bottom Area	-----	40.0mil x	40.0mil
(c) Bonding Pad	-----	100um	
(d) Chip Thickness	-----	11mil	
(e) Junction Height	-----	6.7mil	



AUK Corp.

Eoyang factory, 513-5 Eoyang-dong, Iksan, 570-210, Korea
 Tel. +82 63 839 1111 Fax. +82 63 835 8259
www.auk.co.kr

